Scientific Program

	Afternoon, July 16, 2017
14:00–18:00	Registration (Lobby, International Conference Center of NJU)
18:00–20:00	Reception
Μ	orning, July 17, 2017 Session K (Sanjiang Hall, 三江厅) Chair: Kaiyou Wang (China)
8:30-8:50	Opening
8:50–9:30	TP. Ma (Yale University, USA) Unipolar CMOS Logic: A Transforming Technology for Current and Emerging Transistor Materials
9:30–10:10	Ru Huang (Peking University, China) Emerging Steep Slope Devices for Ultra-Low-Power Applications
10:10–10:20	Conference photo
10:20–11:40	Coffee Break
11:00–11:40	HS. Philip Wong (Stanford University, USA) The N3XT 1,000× of Computing Energy Efficiency
11:40–12:20	Jiangfeng Du (University of Science and Technology of China, China) Quantum control of spins in solids and its applications
12:20–13:30	Lunch
Af	ternoon, July 17, 2017 Session 1 (Zhongda Hall , 中大厅) Chairs: Yang Chai (Hong Kong) / Junichi Murota (Japan)
13:30–14:00	Junichi Murota (Tohoku University, Japan) Atomically Controlled Processing for In-Situ Doping in CVD Si and Ge Epitaxial Growth
14:00–14:30	Deren Yang (Zhejiang University, China) Defects in Cast Quasi-single Crystalline Silicon
14:30–15:00	Seiichi Miyazaki (Nagoya University, Japan) Fabrication of Multiple Stack Si/Ge Quantum Dots for Light/Electron Emission Devices
15:00–15:20	Jimmy Wang (Nanjing University, China) High performance transparent in-plane silicon nanowire Fin-TFTs via a robust nano-droplet-scanning crystallization dynamics
15:20–15:40	Liming Wang (Fudan University, China) Carrier effects on ferromagnetism of Mn-doped Ge Quantum dots
15:40–16:00	Coffee Break
16:00–16:30	Yaoyi Li (Shanghai Jiao Tong University, China) Topological superconductor and Majorana zero mode
16:30–17:00	Yang Chai (The Hong Kong Polytechnic University)

	Extraordinarily Strong Interlayer Interaction and High-Electron-Mobility in 2D Layered PtX_2
17:00–17:20	Yuanhui Sun (Jilin University, China) InSe: a two-dimensional material with strong inter-layer coupling
17:20–17:40	Yi Zhang (Nanjing University, China) Electronic Structures of Novel Quantum Materials: Growth and ARPES Characterizations of Epitaxial Thin Films
18:10–20:00	Banquet
1	Afternoon, July 17, 2017 Session 2 (Yixing Hall, 以行斤) Chairs: Olivier Bonnaud (France) / Durga Misra (USA)
13:30–14:00	Durga Misra (New Jersey Institute of Technology, USA) Solving the Interface Problem in Ge/High-k Gate Stacks
14:00–14:30	Qiliang Li (George Mason University, USA) Graphene Gas Sensors for Chemical Discrimination
14:30–15:00	Tianling Ren (Tsinghua University, China) Novel fabrication method and wearable device applications of graphene
15:00–15:20	Xiaodong Tong (Chinese Academy of Engineering Physics, China) The Optimization of Drain Delay in Short-Chanel GaN HEMT
15:20–15:40	Peng Cui (Shandong University, China) Study of Polarization Coulomb Field Scattering Influence on Improved Linearity in AlGaN/GaN Heterostructure Field-Effect Transistors
15:40-16:00	Coffee Break
16:00–16:30	Olivier Bonnaud (University of Rennes 1, France) Challenge of the semiconductor technologies through innovative education
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16:30–17:00	Olivier Bonnaud (University of Rennes 1, France) Challenge of the semiconductor technologies through innovative education Xiaoyang Zeng (Fudan University, China) High-Performance and Low-Power SoC Design for Information Security Pingan Hu (Harbin Institute of Technology, China) High performance electronics and optoelectronics based on two dimensional
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	Tunable valley splitting in TMDCs by exchange field
14:30–15:00	Zhipei Sun (Aalto University, Finland) Nonlinear photonics with two-dimensional layered materials and their applications
15:00–15:20	Zhongming Wei (Institute of Semiconductors, Chinese Academy of Sciences, China) 2D semiconductors and (opto)electronics based on MoS ₂
15:20–15:40	Xing Sheng (Tsinghua University, China) Implantable Optoelectronic Devices for Deep-Brain Neural Signal Sensing
15:40–16:00	Coffee Break
16:00–16:30	Kevin J Chen (Hong Kong University of Science and Technology, China) GaN-on-Si Power Devices and IC Technology
16:30–17:00	Ming Qiao (University of Electronic Science and Technology of China) Status and Trends of Superjunction Power Semiconductor Devices
17:00–17:20	Shiyong Zhang (Microsystem and Terahertz Research Center, China Academy of Engineering Physics, China) Ka-band power amplifier design using 100nm GaNSi technology
17:20–17:40	Weizong Xu (Nanjing University, China) Low Gate Leakage and High Stability MIS-HEMTs with High-k Y_2O_3 Gate Dielectric
18:10–20:00	Banquet

Morning, July 18, 2017 Session 1 (Zhongda Hall, 中大厅)

Chairs: Bo Shen (China) / Amalia Patane (UK)

- 8:00–8:30 Amalia Patane (University of Nottingham, UK) Novel two-dimensional van der Waals crystals and heterostructures
- 8:30–9:00 Hongtao Yuan (Stanford University, USA) Electric Control of Spin-Coupled Valleytronics in Layered Metal Dichalcogenides
- **9:00–9:20** Tianru Wu (Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, China) Towards the Controllable Synthesis of Graphene, h-BN and Grapheneh-BN Heterostructures
- 9:20–9:40 Haomin Wang (Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, China) Multidimensional Hetero-integration of Graphene and h-BN towards Nanoelectronics
- 9:40–10:00 Coffee Break
- **10:00–10:30** Bo Shen (Peking University, China) Epitaxial growth of GaN-based heterostructures on Si substrates using a large lattice-mismatch induced stress control technology
- **10:30–11:00** Hongxing Wang (Xi'an Jiaotong University, China) Fabrication of microlens arrays for non-planar ultraviolet detector
- **11:00–11:20** Dong Pan (Institute of Semiconductors, Chinese Academy of Sciences) Near full-composition-range high-quality GaAs_{1-x}Sb_x nanowires grown by molecular-beam epitaxy
- 11:20–11:40Ren-Kui Zheng (Shanghai Institute of Ceramics, Chinese Academy of
Sciences)
Reversible and nonvolatile manipulation of the topological surface states of
Cr-doped Bi2Se3 via ferroelectric polarization switching of Pb(Mg1/3Nb2/3)O3-
PbTiO3 single crystals
- 11:40-13:30 Lunch
 - Morning, July 18, 2017 Session 2 (Yixing Hall,以行厅) Chairs: Xue Feng (China) / K. Tsukagoshi (Japan)
- 8:00–8:30 K. Tsukagoshi (National Institute for Materials Science, Japan) Silicon Induced Metal Oxide Thin Film Transistors
- 8:30–9:00 Yong-Young Noh (Dongguk University, Korea) Development of Printed Large Area Organic Transistors and Integrated Circuits
- **9:00–9:20** Fukai Shan (Qingdao University, China) Solution-processed ternary p-type CuCrO2 semiconductors and their applications in thin-film transistors
- 9:20–9:40 Xiaoci Liang (Sun Yat-Sen University, China) Performance Adjustments of Solution Combustion-Processed In-Zn-O TFTs through Defect Engineering

9:40–10:00	Coffee Break
10:00–10:30	Xue Feng (Tsinghua University, China) Epidermal Inorganic Optoelectronics for blood oxygen measurement
10:30–11:00	Qing Chen (Peking University, China) The structure-dependent properties of InAs nanowires and their devices
11:00–11:20	Xiangyang Shi (Chinese Academy of Engineering Physics) Advanced In _{0.8} Ga _{0.2} As/AIAs Resonant Tunneling Diode with High Peak Current Density for Terahertz Radiation
11:20–11:40	Hailong Wang (Institute of Semiconductors, Chinese Academy of Sciences) Complete demagnetization of (Ga,Mn)As films via electric field
11:40–13:30	Lunch
I	Morning, July 18, 2017 Session 3 (Jiexing Hall, 洁行厅) Chairs: Shijie Xu (Hong Kong) / Buwen Cheng (China)
8:00–8:30	Buwen Cheng (Institute of Semiconductors, CAS, China) Si-based heterostructure photodetectors for long-wavelength applications
8:30–9:00	Ning Dai (Shanghai Institute of Technical Physics, CAS, China) Fabrication of Flexible Bismuth Telluride Films and Investigation on Their Photoelectric Properties
9:00–9:20	Yulian Cao (Institute of Semiconductors, Chinese Academy of Sciences) Mid-infrared InAs-based interband cascade lasers
9:20–9:40	Young Huang (Oxford Instruments)
9:40–10:00	Coffee Break
10:00–10:30	Shijie Xu (The University of Hong Kong, China) The self-absorption effect in excitonic luminescence of ZnO
10:30–11:00	Hai Lu (Nanjing University, China) High performance UV photodetectors based on wide bandgap semiconductors
11:00–11:20	Han Wu (Nanjing University, China) Cathodoluminescence spectra of monolayer phosphorene on different substrates
11:20–11:40	Yongheng Huo (University of Science and Technology of China, China) Spontaneous brightening of dark excitons in GaAs/AlGaAs quantum dots near a cleaved facet
11:40–13:30	Lunch
Af	iternoon, July 18, 2017 Session 1 (Zhongda Hall, 中大厅)

Chairs: Weifeng Sun (China) / E. A. Fitzgerald (USA) 13:30–14:00 Rong Zhang (Shandong University, China) Manipulable and hybridized, ultralow-threshold lasing in a plasmonic laser

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using elliptical InGaN/GaN nanorods

14:00–14:30	Eugene A. Fitzgerald (MIT, USA) Silicon Integrated Circuit Innovation Defined by New Materials
14:30–14:50	Jiacai Nie (Beijing Normal University, China) Possible Unconventional Pairing Mechanism at Superconducting LaAIO ₃ /SrTiO ₃ Interface
14:50–15:10	Yunbin He (Hubei University, China) SnO ₂ epitaxial films with varying thickness on c-sapphire: structure evolution and optical band gap modulation
15:10–15:30	Coffee Break
15:30–16:00	Tangsheng Chen (Nanjing Electronic Devices Institute, China) Development of High Voltage SiC MOSFET
16:00–16:30	Weifeng Sun (Southeast University, China) Technical Challenge of Power Integrated Devices and New Structures in Monolithic Power ICs
16:30–16:50	Rong WANG (Institute of Electronic Engineering, China Academy of Engineering Physics, China) First-principles study on the role of fluorine impurities in the performance of enhancement-mode AIGaN/GaN HEMTs
16:50–17:10	Jun-Wei Luo (National Center for Nanoscience and Technology, China) Photocorrosion-limited maximum efficiency of solar photoelectrochemical water splitting
17:10–17:30	Zonghai Hu (Beijing University of Posts and Telecommunications, China) Pristine graphene as a catalyst
17:30-19:30	Poster Session
18:00–20:00	Buffet dinner
ŀ	Afternoon, July 18, 2017 Session 2 (Yixing Hall, 以行斤) Chairs: Jingbi You (China) / Helmut Baumgart (USA)
13:30–14:00	Helmut Baumgart (Old Dominion University, USA) Improving Conversion Efficiency of Thermoelectric Materials with Novel Phonon Engineering Approaches
14:00–14:30	Guozhen Shen (Institute of Semiconductors, CAS, China) Flexible Microsupercapacitors and Their Applications in Integrated Sensing Systems
14:30–15:00	Xiaodan Zhang (Nankai University, China) Key Issues in High Efficient Perovskite/Silicon-Heterojunction Two-Terminal Tandem Solar Cells
15:00–15:20	Lijun Zhang (Jilin University, China) Design of Inorganic Pb-free Halide Double-perovskite Semiconductors for Solar Cells via Cation-transmutation
15:20–15:40	Coffee Break

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16:10–16:40	Hongwei Han (Wuhan University, China) Stable Fully Printable perovskite solar cells based on triple mesoscopic layers
16:40–17:10	Yabing Qi (Okinawa Institute of Science and Technology, Japan) A Surface Science Approach to Perovskite Material and Solar Cell Research
17:10–17:30	Dongwen Yang (Jilin University, China) Functionality-Directed Screening of Pb-Free Hybrid Organic–Inorganic Perovskites with Desired Intrinsic Photovoltaic Functionalities
17:30-19:30	Poster Session
18:00–20:00	Buffet dinner
A	Afternoon, July 18, 2017 Session 3 (Jiexing Hall, 洁行厅) Chairs: Jie Yao (USA) / Fei Ding (Germany)
13:30–14:00	Fengqi Liu (Institute of Semiconductors, CAS, China) Quantum Cascade Lasers: From Mid-infrared to THz
14:00–14:30	Fei Ding (Leibniz University Hannover, Germany) Towards an ideal entangled photon source
14:30–14:50	Huiying Huang (Johannes Kepler University, Austria) Electrical-driven- GaAs/AlGaAs-QD-device with electroluminescence energy tunable around ⁸⁷ Rb D2 line
14:50–15:10	Jun Zhang (Institute of Semiconductors, CAS, China) Laser cooling and quantum control of semiconductor phonons
15:10–15:30	Coffee Break
15:30–16:00	Jie Yao (UC Berkeley, USA) Tunable Optical Responses near the 2D limit
16:00–16:20	Chong-Xin Shan (Zhengzhou University, China) Chemical Vapor Deposited Diamond for Solar-blind Photodetectors
16:20–16:40	Shusheng Pan (Institute of Solid State Physics, Chinese Academy of Sciences, China) High Detectivity UV Photodetector Based on Intermediate Band Bi _x Sn _{1-x} O ₂
16:40–17:00	Huijun Tian (Beijing University of Technology, China) Hybrid GaN-graphene ultraviolet photodetectors
17:30-19:30	Poster Session
18:00-20:00	Buffet dinner

Morning, July 19, 2017 Session K (Sanjiang Hall, 三江厅) Chair: Xinran Wang (China)

8:00–8:45	Akira Toriumi (University of Tokyo, Japan) Materials fundamentals for germanium CMOS
8:45–9:30	Wei Huang (Nanjing Tech University, China) Recent Advances in Organic Optoelectronics
9:30–9:50	Coffee Break
9:50–10:35	Ming Liu (Institute of Microelectronics, CAS, China) Developing Status and Trend for Nonvolatile Memory
10:35–11:20	Yue Kuo (Texas A&M University, USA) Semiconductor Technology – Nano, Giga, and Beyond
11:20–12:00	Closing Remark
12:00–13:30	Lunch
	Afternoon, July 19, 2017
13:30–18:00	Tour (Nanjing Museum)
18:00–20:00	Buffet dinner